BUR920000156US3

AMENDMENTS TO THE CLAIMS:

1.- 39 (Cancelled) Claims 1 through 39 have been cancelled.

40. (Currently Amended) A poly-poly capacitor comprising a bottom polysilicon electrode formed over an isolation ~~regions~~ region that ~~are~~ is present in a Si-containing substrate; a high-k dielectric having a dielectric constant of greater than about 8 formed on a portion of said bottom electrode; and a doped Si-containing electrode formed on said high-k dielectric, wherein said bottom electrode, said high-k dielectric and a portion of said doped Si-containing electrode form a capacitor and another portion of said doped Si-containing electrode comprises an intrinsic base ~~polysilicon~~ layer of ~~a~~ an abutting bipolar device.

41. (Original) The poly-poly capacitor of Claim 40 wherein said bottom polysilicon electrode is composed of poly SiGe.

42. (Original) The poly-poly capacitor of Claim 40 wherein said high-k dielectric is a binary metal oxide, silicate, aluminate or oxynitride of a binary metal oxide, or a perovskite oxide.

43. (Original) The poly-poly capacitor of Claim 42 wherein said high-k dielectric is a binary metal oxide or an aluminate of a binary metal oxide.

44. (Original) The poly-poly capacitor of Claim 43 wherein said high-k dielectric is Al_2O_3.

BUR920000156US3

45. (Original) The poly-poly capacitor of Claim 40 wherein said doped Si-containing electrode is comprised of poly SiGe.

46. (Original) The poly-poly capacitor of Claim 40 wherein spacers are present on any exposed sidewalls of said high-k dielectric and said doped Si-containing electrode.

47. (Original) The poly-poly capacitor of Claim 40 wherein a diffusion barrier layer is present between said bottom electrode and said high-k dielectric, between said high-k dielectric and said doped Si-containing electrode, or between said bottom electrode and said high-k dielectric and between said high-k dielectric and said doped Si-containing electrode.